WBA0030L 20 - 3000 MHz LOW NOISE WIDE BAND AMPLIFIER

Key Features



- 20 ~ 3000 MHz
- 3.0 dB Noise Figure
- 40.0 dBm Output IP₃
- 22.0 dB Gain
- +/-0.60 dB Gain Flatness
- 24.0 dBm P_{1dB}
- 1.5:1 VSWR
- Single Power Supply
- >34 Years MTBF
- Unconditional Stable
- RoHS compliant
- ROHS compliant

Product Description

WBA0030L integrates WanTcom proprietary low noise amplifier technology, high frequency micro electronic assembly techniques, and high reliability design to realize optimum low noise figure, wideband, high linearity, and unconditional stable performances together. With single +10.0V DC operation, the amplifier has optimal input and output matching in the specified frequency range at 50-Ohm impedance system. The amplifier has standard SMA connectorized WP-5 gold plated housing.

The amplifier is designed to meet the rugged standard of MIL-STD-202.

Applications

- Mobile Infrastructures
- GPS
- CATV/DBS
- PCS
- 3G
 - Measurement
- LTE



Specifications

Summary of the electrical specifications WBA0030L at room temperature

Index	Testing Item	Symbol	Test Constraints	Min	Nom	Max	Unit
1	Gain	S ₂₁	20 – 3000 MHz	20	22		dB
2	Gain Variation	ΔG	20 – 3000 MHz		+/- 0.5	+/-1.0	dB
3	Input VSWR	SWR ₁	20 – 3000 MHz		1.5:1	2:1	Ratio
4	Output VSWR	SWR ₂	20 – 3000 MHz		1.5:1	2:1	Ratio
5	Reverse Isolation	S ₁₂	20 – 3000 MHz		40		dB
	Naiaa figura	NF	200 – 3000 MHz		3.2	3.8	dB
6	Noise figure	INF	10 – 200 MHz			5.0	dB
7	Output Power 1dB compression Point	P _{1dB}	1.0 – 3000 MHz	22	24		dBm
8	Output-Third-Order Interception point	IP ₃	Two-Tone, Pout +0 dBm each, 1 MHz separation	36	40		dBm
9	Current Consumption	l _{dd}	V _{dd} = +10 V		250		mA
10	Power Supply Voltage	V _{dd}		+9.5	+10	+10.5	V
11	Thermal Resistance	R _{th,c}	Junction to case			30	°C/W
12	Operating Temperature	To		-40		+85	°C
13	Maximum Average RF Input Power	P _{IN, MAX}	DC – 6.0 GHz			30	dBm

Absolute Maximum Ratings

Parameters	Units	Ratings
DC Power Supply Voltage	V	12.0
Drain Current	mA	300
Total Power Dissipation	W	3
RF Input Power	dBm	30
Channel Temperature	°C	150
Storage Temperature	°C	-55 ~ 125
Operating Temperature	°C	-40 ~ 85
Thermal Resistance	°C/W	30

Operation of this device above any one of these parameters may cause permanent damage.

Ordering Information

Model Number

WBA0030L



RF INPLIT

Specifications and information are subject to change without notice.

Functional Block Diagram

Control Circuitry

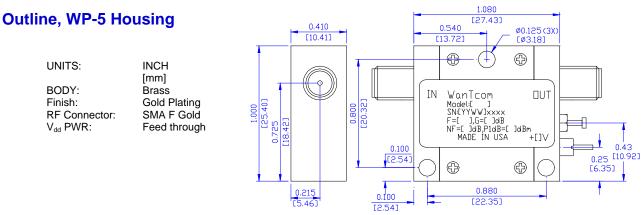
RF OUTPUT

+V_{dd} IN

RF & DC GND



Typical Data



Application Notes:

A. SMA Torque Wrench Selection

Always use a torque wrench with $5 \sim 6$ inch-lb coupling torque setting for mating the SMA cables to the amplifier. Never use torque more than 8 inch-lb wrench for tightening the mating cable to the connector. Otherwise, the permanent damage will occur to the SMA connectors of the amplifier. 8710-1582 (5 inch-lb) is one of the ideal torque wrench choice from Agilent Technology.

B. DC Power Line Connection

Strip the insulation layer at the end of DC power supply wire. The stripped distance should be in the range of 0.100" to 0.200". The $24 \sim 26$ American Wire Gauge wire is suitable. Wound the stripped terminal wire about 1 to 2 turns on the DC feed thru center pin. Solder the wounded wire and the center pin together. Clean the soldering area by Q-tip with alcohol to remove the flux and residue.

Repeat the process to solder the DC return wire on the ground turret.

C. Mounting the Amplifier

Use three pieces of #4-40 with longer than 9/16" screws for mounting the amplifier on a metal-based chase. Flat and spring washers are needed to prevent the screw loosening during the shock and vibration. Always use the appropriate torque setting of the power screwdriver to mount them.

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